

Silicon NPN Power Transistors

2N6671 2N6672 2N6673

DESCRIPTION

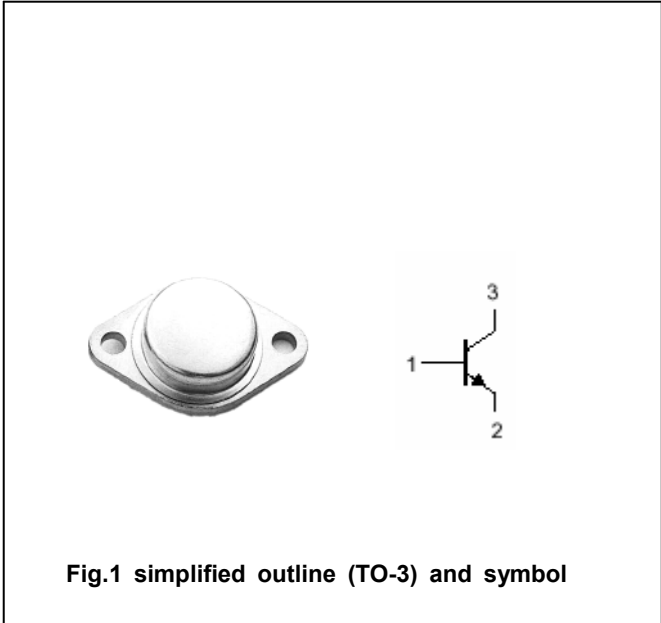
- With TO-3 package
- Low saturation voltage
- Fast switching speed
- High voltage ratings

APPLICATIONS

- Off-line power supplies
- High-voltage inverters
- Switching regulators

PINNING

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector



Absolute maximum ratings(Ta=□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V _{CBO}	Collector-base voltage	2N6671	450	V
		2N6672	550	
		2N6673	650	
V _{CEO}	Collector-emitter voltage	2N6671	300	V
		2N6672	350	
		2N6673	400	
V _{EBO}	Emitter-base voltage	Open collector	8	V
I _C	Collector current		8	A
I _{CM}	Collector current-peak		10	A
I _B	Base current		4	A
P _D	Total Power Dissipation	T _C =25□	150	W
T _j	Junction temperature		200	□
T _{stg}	Storage temperature		-65~200	□

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CHARACTERISTICS

T_j=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT	
V _{CEO(SUS)}	Collector-emitter sustaining voltage	2N6671	300			V	
		2N6672	350				
		2N6673	400				
V _{CEsat-1}	Collector-emitter saturation voltage	I _C =5A; I _B =1A			1.0	V	
V _{CEsat-2}	Collector-emitter saturation voltage	I _C =8A; I _B =4A			2.0	V	
V _{BEsat}	Base-emitter saturation voltage	I _C =5A; I _B =1A			1.6	V	
I _{CEV}	Collector cut-off current	2N6671	V _{CE} =450V; V _{BE(off)} =-1.5V			0.1	mA
		2N6672	V _{CE} =550V; V _{BE(off)} =-1.5V				
		2N6673	V _{CE} =650V; V _{BE(off)} =-1.5V				
I _{EBO}	Emitter cut-off current	V _{EB} =8V; I _C =0			2.0	mA	
h _{FE}	DC current gain	I _C =5A; V _{CE} =3V	10		40		
C _{OB}	Output capacitance	I _E =0; V _{CB} =10V; f=0.1MHz			300	pF	
f _T	Transition frequency	I _C =0.2A; V _{CE} =10V	15		60	MHz	

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	VALUE	UNIT
R _{th j-c}	Thermal resistance junction to case	1.17	°C/W

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PACKAGE OUTLINE

